

ABSTRACT OF THE DISCLOSURE

In a semiconductor laser device having an oscillation wavelength of larger than 760 nm and smaller than 800 nm,  
5 on an n-type GaAs substrate (101), there are stacked in sequence an n-type first and second lower cladding layers (103, 104), a lower guide layer (105), a GaAs lower interface protective layer (106), an InGaAsP strained multiquantum well active layer (107), a GaAs upper  
10 interface protective layer (108), an upper guide layer (109) and a p-type upper cladding layer (110). An interface between the quantum well active layer (107) and the upper guide layer (109), and an interface between the quantum well active layer (107) and the lower guide layer  
15 (105) become steep, and also epitaxy growth of crystals becomes favorable.